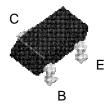


FSB660 / FSB660A



SuperSOT[™]-3 (SOT-23)

PNP Low Saturation Transistor

These devices are designed with high current gain and low saturation voltage with collector currents up to 2A continuous.

Absolute Maximum Ratings* T_{A = 25°C unless otherwise noted}

Symbol	Parameter	FSB660/FSB660A	Units
V _{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current - Continuous	2	Α
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150°C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics _____ T_A = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		FSB660/FSB660A	
P _D	Total Device Dissipation	500	mW
R _{θJA}	Thermal Resistance, Junction to Ambient	250	°C/W

PNP LOW Saturation Transis	PNP	turation Transisto
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(continued)

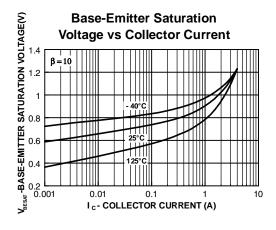
Electrical Characteristics

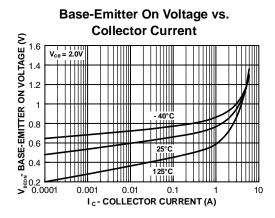
T_{A = 25°C} unless otherwise noted

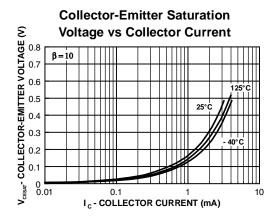
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAI	RACTERISTICS				
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA	60		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 100 μA	60		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 100 μA	5		V
I _{CBO}	Collector Cutoff Current	V _{CB} = 30 V		100	nA
		V _{CB} = 30 V, T _A =100°C		10	uA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V		100	nA
ON CHAR	ACTERISTICS*				
h _{FE}	DC Current Gain	I _C = 100 mA, V _{CE} = 2 V	70		-
		I _C =500mA, V _{CE} =2V FSB660	100	300	
		FSB660A	250	550	
		I _C = 1 A, V _{CE} = 2 V	80		
		I _C = 2 A, V _{CE} = 2 V	40		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		300	mV
02(001)		I _C = 2 A, I _B =200 mA FSB660		350	
		FSB660A		300	
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		1.25	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 1 A, V _{CE} = 2 V		1	V
SMALL SI	GNAL CHARACTERISTICS				
C _{obo}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1MHz		30	pF
f _T	Transition Frequency	I _C = 100 mA,V _{CE} = 5 V, f=100MHz	75		-

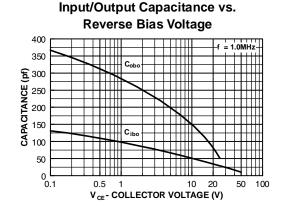
*Pulse Test: Pulse Width $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%$

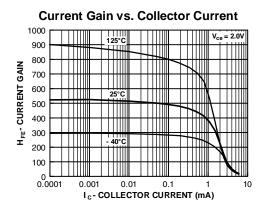
Typical Characteristics

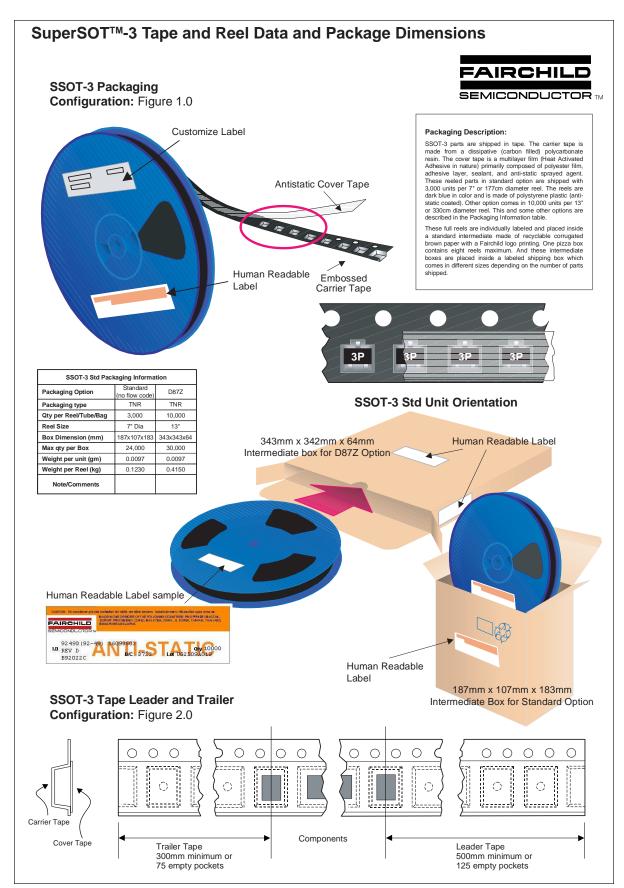








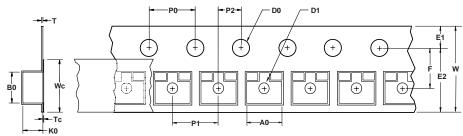


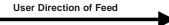




SSOT-3 Embossed Carrier Tape

Configuration: Figure 3.0



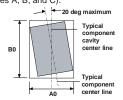


Dimensions are in millimeter														
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-3 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-02

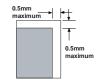
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

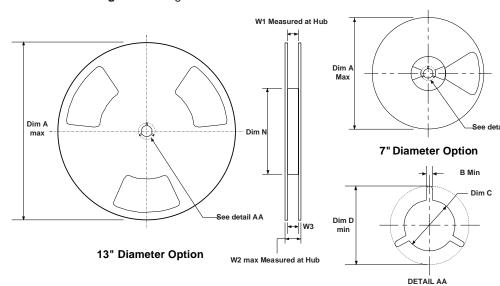


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

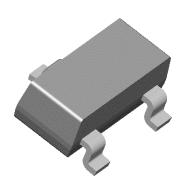
SSOT-3 Reel Configuration: Figure 4.0

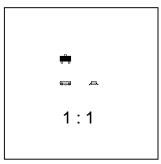


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SuperSOT™-3 Tape and Reel Data and Package Dimensions, continued

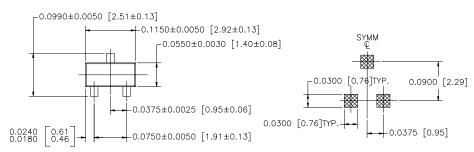
SuperSOT™-3 (FS PKG Code 32)



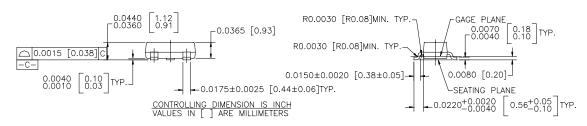


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0097



LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

SUPER SOT , 3 LEADS

- 1. STANDARD LEAD FINISH TO BE 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
- 2. NO JEDEC REGISTRATION AS OF DEC. 1995.

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